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## Sommario/riassunto

In August 1940 Australia had been at war for almost a year when a Hudson bomber - the A16-97 - carrying ten people, including three cabinet ministers, crashed into a ridge near Canberra. In the ghastly inferno that followed the crash, the nation lost its key war leaders. Over the next twelve months, it became clear that the passing of Geoffrey Street, Sir Henry Gullett and James Fairbairn had destabilized Robert Menzies' wartime government. As a direct but delayed consequence, John Curtin became prime minister in October 1941. Controversially, t

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Electrostatic discharge (ESD) failure mechanisms continue to impact semiconductor components and systems as technologies scale from micro- to nano-electronics. This book studies electrical overstress, ESD, and latchup from a failure analysis and case-study approach. It provides a clear insight into the physics of failure from a generalist perspective, followed by investigation of failure mechanisms in specific technologies, circuits, and systems. The book is unique in covering both the failure mechanism and the practical solutions to fix the problem from either a technology or circuit method